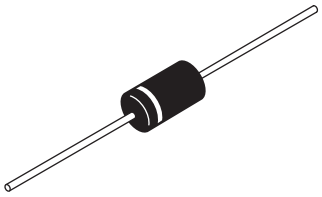
Schottky Rectifier
1.1 A

11DQ09,11DQ09-M3,11DQ10,11DQ10-M3

Vishaymas Semiconductors



DO-204AL

FEATURES

- Low profile, axial leaded outline
- High frequency operation
- Very low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for commercial level
- Halogen-free according to IEC 61249-2-21 definition (-M3 only)

DESCRIPTION

The VS-11DQ... axial leaded Schottky rectifier has been optimized for very low forward voltage drop, with moderate leakage. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

PRODUCT SUMMARY	
Package	DO-204AL (DO-41)
$I_{F(AV)}$	1.1 A
V_R	90 V, 100 V
V_F at I_F	See Electrical table
I_{RM}	1.0 mA at 125 °C
T_J max.	150 °C
Diode variation	Single die
E_{AS}	1.0 mJ

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	**CHARACTERISTICS**	**VALUES**	**UNITS**
$I_{F(AV)}$	Rectangular waveform	1.1	A
V_{RRM}		90/100	V
I_{FSM}	t_p = 5 µs sine	85	A
V_F	1 Apk, T_J = 25 °C	0.85	V
T_J	Range	- 40 to 150	°C

VOLTAGE RATINGS						
PARAMETER	**SYMBOL**	**VS-11DQ09**	**VS-11DQ09-M3**	**VS-11DQ10**	**VS-11DQ10-M3**	**UNITS**
Maximum DC reverse voltage	V_R	90	90	100	100	V
Maximum working peak reverse voltage	V_{RWM}					

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**VALUES**	**UNITS**
Maximum average forward current See fig. 4	$I_{F(AV)}$	50 % duty cycle at T_C = 75 °C, rectangular waveform		1.1	A
Maximum peak one cycle non-repetitive surge current See fig. 6	I_{FSM}	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated V_{RRM} applied	85	
		10 ms sine or 6 ms rect. pulse		14	
Non-repetitive avalanche energy	E_{AS}	T_J = 25 °C, I_{AS} = 0.5 A, L = 8 mH		1.0	mJ
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 µs Frequency limited by T_J maximum V_A = 1.5 x V_R typical		0.5	A

ELECTRICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop See fig. 1	V_{FM} (1)	1 A	T_J = 25 °C	0.85	V
		2 A		0.96	
		1 A	T_J = 125 °C	0.68	
		2 A		0.78	
Maximum reverse leakage current See fig. 2	I_{RM} (1)	T_J = 25 °C	V_R = Rated V_R	0.5	mA
		T_J = 125 °C		1.0	
Typical junction capacitance	C_T	V_R = 5 V_{DC} (test signal range 100 kHz to 1 MHz) 25 °C		35	pF
Typical series inductance	L_S	Measured lead to lead 5 mm from package body		8.0	nH
Maximum voltage rate of change	dV/dt	Rated V_R		10 000	V/µs

Note

(1) Pulse width < 300 µs, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J (1), T_{Stg}		- 40 to 150	°C
Maximum thermal resistance, junction to ambient	R_{thJA}	DC operation Without cooling fin	100	°C/W
Typical thermal resistance, junction to lead	R_{thJL}	DC operation See fig. 4	81	
Approximate weight			0.33	g
			0.012	oz.
Marking device		Case style DO-204AL (DO-41)	11DQ09	
			11DQ10	

Note

(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

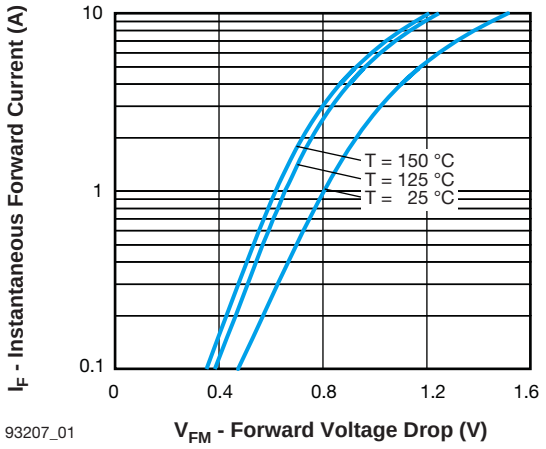


Fig. 1 - Maximum Forward Voltage Drop Characteristics

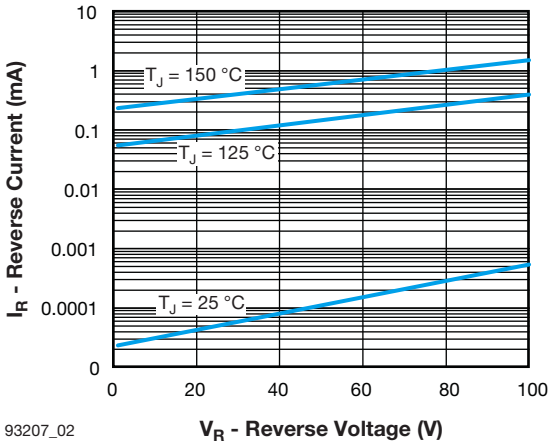


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

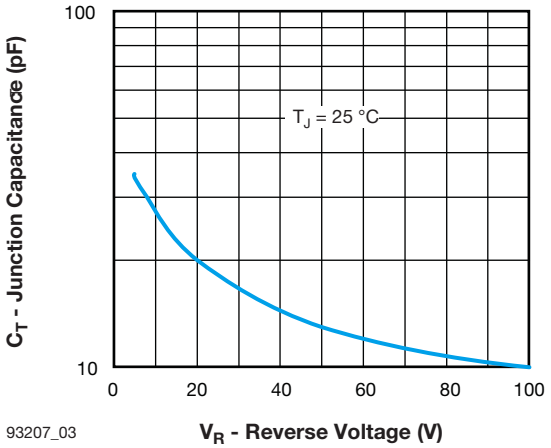


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

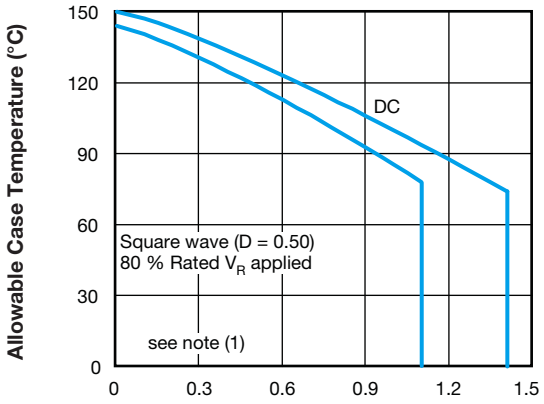


Fig. 4 - Maximum Ambient Temperature vs. Average Forward Current

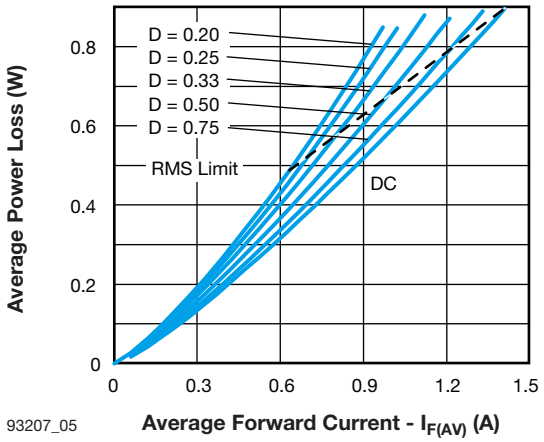


Fig. 5 - Forward Power Loss Characteristics

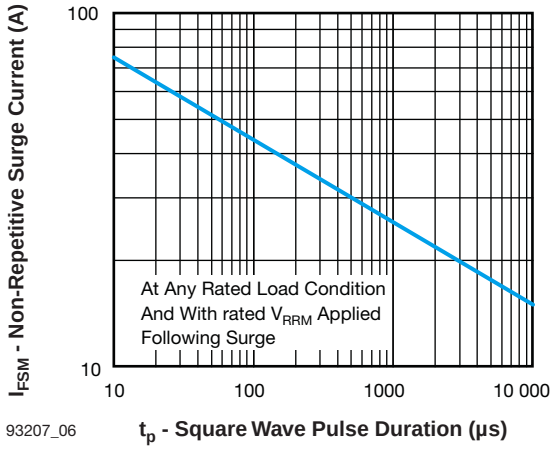


Fig. 6 - Maximum Non-Repetitive Surge Current

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}$/D) (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = 80 % rated V_R

Axial DO-204AL (DO-41)

DIMENSIONS in millimeters (inches)